

ABSTRACT OF THE DISCLOSURE

A method of forming a semiconductor device comprising: sequentially forming a supporting layer and a sacrificial layer over a semiconductor substrate; forming an opening by patterning the sacrificial layer and the supporting layer; forming a bottom electrode covering the inner wall and the bottom of the opening; removing the sacrificial layer by a wet etch process; and forming a dielectric layer and an upper electrode on the bottom electrode and the supporting layer, wherein the sacrificial layer is formed of a material having a faster wet etch rate than the supporting layer.

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